Document No. : IAP-SS71A-00

APPROVAL SHEET

Product	Battery Protect Solution IC
Product code	**SS71A** (001-SS71A-00)
Production Form	UTEP - 6LS, BD3.4x2.53
Date of Registration	December. 20. 2013

	Issued	Checked	Checked	Approved
결재				
	2/5	2/5	2/5	2/5

협의	개발	품질		
	2/5	2/5		

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Contents

Features

1. The protection IC and The Dual-Nch MOSFET to use common Drain are integrated into One-packaging IC.
2. Reduced Pin-Count by fully connecting internally.
3. Application Part

1) Protection IC

① Uses high withstand voltage CMOS process.
- The charger section can be connected up to absolute maximum rating 28V.

② Detection voltage precision
- Overcharge detection voltage

±25㎷ (Ta=25℃), ±45㎷ (Ta=-30~70℃)
- Overdischarge detection voltage

±70㎷ (Ta=25℃), ±80㎷ (Ta=-30~70℃)
- Discharging overcurrent detection voltage

±10㎷ (Ta=25℃), ±20㎷ (Ta=-30~70℃)
- Charging overcurrent detection voltage

±10㎷ (Ta=25℃), ±20㎷ (Ta=-30~70℃)

③ Built-in detection delay times
- Overcharge detection delay time

1.00±0.20s (Ta=25℃), 1.00[+0.50, −0.40]s (Ta=-30~70℃)
- Overdischarge detection delay time)

20.0±4.0㎳ (Ta=25℃), 20.0[+10.0, −8.0]㎳ (Ta=-30~70℃)
- Discharging overcurrent detection delay time)

12.0±2.4㎳ (Ta=25℃), 12.0[+6, −4.8]㎳ (Ta=-30~70℃)
- Charging overcurrent detection delay time)

16.6±3.8㎳ (Ta=25℃), 16.6[+8.4, −7.0]㎳ (Ta=-30~70℃)
- Short detection delay time)

400[+160, −170]㎲ (Ta=25℃), 400[+400, −220]㎲ (Ta=-30~70℃)

④ With abnormal charger detection function.

⑤ 0V charge function is allowed

⑥ Auto Wake-up function is allowed

2) FET

① Using advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltage as low as 2.5V while retaining a 12V $V_{GS(MAX)}$.

② The protection for ESD

③ Common drain configuration

④ General characteristics
- V_{DS} (V) = 24V
- I_D (A) = 7A
- $R_{SS(ON)}$ < 19mΩ (V_{GS} = 3.9V, I_D = 1A)
- ESD Rating : 2000V HBM

Outline

This is a battery protect solution IC which is integrated with built-in the protection IC to use a lithium ion/lithium polymer secondary batteries developed for 1-cell series and Dual-Nch MOSFET. It functions to protect the battery by detecting overcharge, overdischarge, discharge overcurrent, charge overcurrent and other abnormalities as turning off internal Nch MOSFET. The protection IC is composed of four voltage detectors, short detection circuit, reference voltage sources, oscillator, counter circuit and logical circuits.

The C_{OUT} pin (charge FET control pin) and D_{OUT} pin (discharge FET control pin) outputs are CMOS output, and can drive the internal Nch MOSFET directly. The C_{OUT} output becomes low level after delay time fixed in the IC if overcharge is detected. The D_{OUT} output becomes low level after delay time fixed in the IC if overdischarge, discharge overcurrent or short is detected.

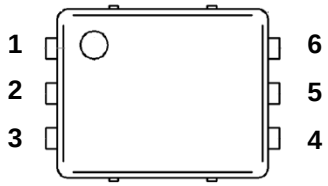
On overcharge state, if the V_{DD} voltage is less than the overcharge release voltage, the C_{OUT} output becomes high level after delay time fixed in the IC. On overdischarge state, if the voltage of the battery rises more than the overdischarge detection voltage with connecting the charger, the D_{OUT} output becomes high level after delay time fixed in the IC. Charging current can be supplied to the battery discharged up to 0V.

Once discharge overcurrent or short have been detected, if the state of discharge overcurrent or short is released by opening the loads, the D_{OUT} output becomes high level after delay time fixed in the IC. On overdischarge state, the supply current is reduced as less as possible. Once charge overcurrent has been detected, the state of charge overcurrent is released by opening the charger and setting the load.

Pin Assignment

[Package : UTEP-6LS]

<Top view>



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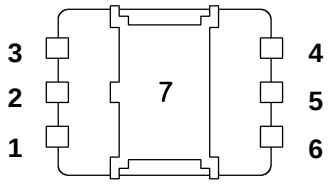
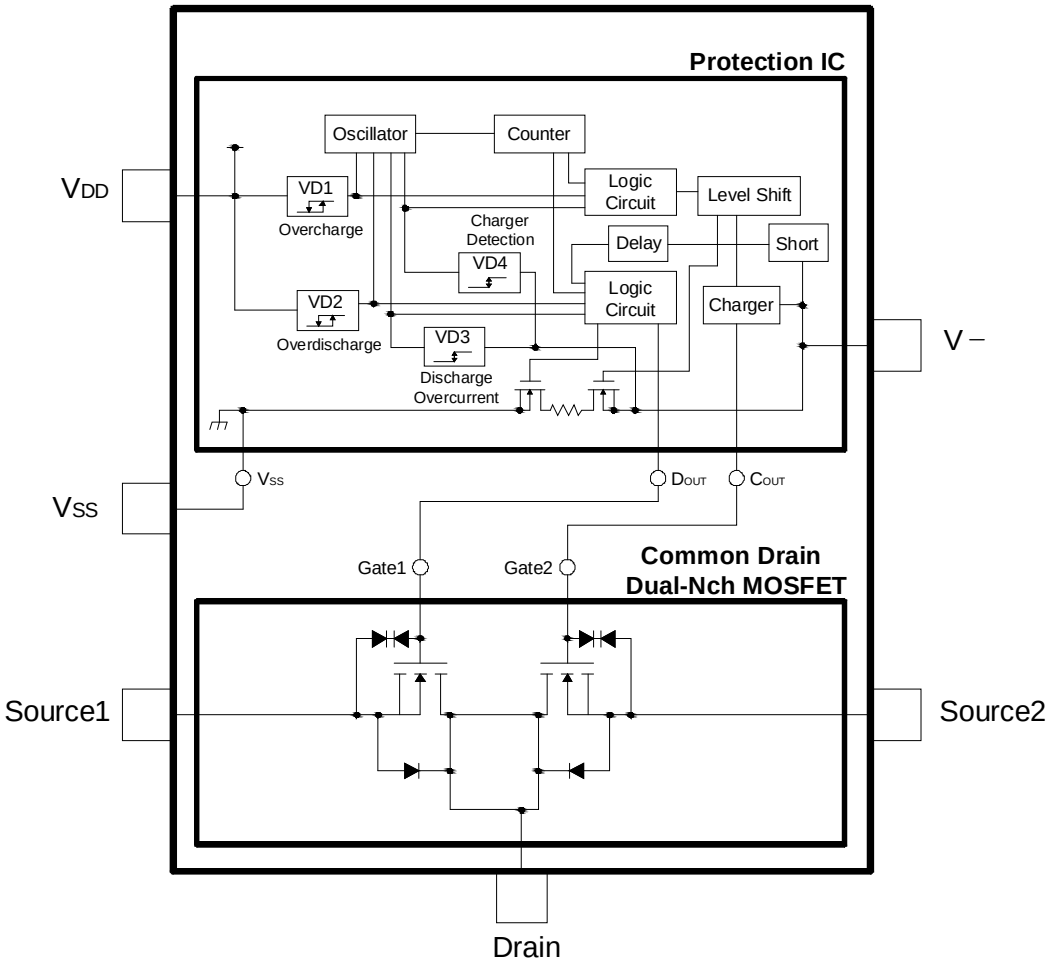


1	Source 1
2	Vss
3	V_{DD}
4	V-
5	N.C. (No Connect)
6	Source 2
7	Drain

Block Diagram



Absolute Maximum Rating

※ T_{OPR}=25℃, V_{SS}=0V

Item	Symbol	Rating	Unit
Supply Voltage	V_{DD}	-0.3 ~ 12	V
V- Terminal Input Voltage	V-	V_{DD}-28 ~ V_{DD}+0.3	V
C_{OUT} Terminal Output Voltage	V_{COUT}	V_{DD}-28 ~ V_{DD}+0.3	V
D_{OUT} Terminal Output Voltage	V_{DOUT}	V_{SS}-0.3 ~ V_{DD}+0.3	V
Operation Temperature	T_{OPR}	-40 ~ +85	℃
Storage Temperature	T_{STG}	-55 ~ +125	℃
Drain-Source Voltage	V_{DS}	24	V
Gate-Source Voltage	V_{GS}	±12	V

Electrical Characteristics

Item	Symbol	Measure Condition		Min.	Typ.	Max.	Unit	*1
Input Voltage								
Operating Input Voltage	$V_{DD}1$	V_{DD} - V_{SS}		1.5	-	10.0	V	A
Minimum Operating Voltage for 0V Charging	V_{ST}	V_{DD} − V-, V_{DD}-V_{SS}=0V		-	-	1.2	V	A
Channel ON Voltage								
C_{OUT} Pin Nch ON Voltage	$V_{OL}1$	I_{OL}=30μA, V_{DD}=4.5V		-	0.4	0.5	V	-
C_{OUT} Pin Pch ON Voltage	$V_{OH}1$	I_{OH}= -30μA, V_{DD}=3.9V		3.4	3.7	-	V	-
D_{OUT} Pin Nch ON Voltage	$V_{OL}2$	I_{OL}=30μA, V_{DD}=2.0V		-	0.2	0.5	V	-
D_{OUT} Pin Pch ON Voltage	$V_{OH}2$	I_{OL}= -30μA, V_{DD}=3.9V		3.4	3.7	-	V	-
Current Consumption								
Current Consumption	I_{DD}	V_{DD}=3.9V, V-=0V		-	-	6.0	μA	L
			T_{OPR}= -30~70℃	-	-	-		
Current Consumption at Stand-By	I_S	V_{DD}=2.0V		-	-	0.5	μA	L
			T_{OPR}= -30~70℃	-	-	-		
Over Charge Voltage Protection								
Overcharge Detection Voltage	$V_{DET}1$	R1=1.0kΩ	T_{OPR}= 25℃	4.400	4.425	4.450	V	B
			T_{OPR}= -30~70℃	4.380	4.425	4.470		
Overcharge Detection Delay Time	$tV_{DET}1$	V_{DD}=3.6V→4.6V	T_{OPR}= 25℃	0.80	1.00	1.20	s	B
			T_{OPR}= -30~70℃	0.60	1.00	1.50		
Overcharge Release Voltage	$V_{REL}1$	R1=1.0kΩ	T_{OPR}= 25℃	4.185	4.225	4.265	V	B
			T_{OPR}= -30~70℃	4.155	4.225	4.295		
Overcharge Release Delay Time	$tV_{REL}1$	V_{DD}=4.6V→3.6V	T_{OPR}= 25℃	12.8	16.0	19.2	ms	B
			T_{OPR}= -30~70℃	9.6	16.0	24.0		

Item	Symbol	Measure Condition		Min.	Typ.	Max.	Unit	*1
Over Discharge Voltage Protection								
Overdischarge Detection Voltage	$V_{DET}2$	R1=1.0kΩ V-=0V	T_{OPR}= 25℃	2.430	2.500	2.570	V	D
			T_{OPR}= -30~70℃	2.420	2.500	2.580		
Overdischarge Detection Delay Time	$tV_{DET}2$	V_{DD}=3.6V→2.2V	T_{OPR}= 25℃	16.0	20.0	24.0	ms	D
			T_{OPR}= -30~70℃	12.0	20.0	30.0		
Overdischarge Release Voltage	$V_{REL}2$	R1=1.0kΩ	T_{OPR}= 25℃	2.810	2.900	2.990	V	D
			T_{OPR}= -30~70℃	2.800	2.900	3.000		
Overdischarge Release Voltage 2	$V_{REL}2'$	Vchg = 4.2V R1=1.0kΩ	T_{OPR}= 25℃	2.430	2.520	2.610	V	D
			T_{OPR}= -30~70℃	2.420	2.520	2.620		
Overdischarge Release Delay Time	$tV_{REL}2$	V_{DD}=2.2V→3.6V	T_{OPR}= 25℃	0.8	2.8	4.8	ms	E
			T_{OPR}= -30~70℃	0.5	2.8	6.0		
Discharge Overcurrent Protection								
Discharging Overcurrent Detection Voltage	$V_{DET}3$	V_{DD}=3.0V R2=2.2kΩ	T_{OPR}= 25℃	0.115	0.125	0.135	V	F
			T_{OPR}= -30~70℃	0.105	0.125	0.145		
Discharging Overcurrent Detection Current	$I_{DET}3$	# Reference : 1) Discharge / Charge Overcurrent Characteristics						
Discharging Overcurrent Detection Delay Time	$tV_{DET}3$	V_{DD}=3.0V V-=0V→0.3V	T_{OPR}= 25℃	9.6	12.0	14.4	ms	F
			T_{OPR}= -30~70℃	7.2	12.0	18.0		
Discharging Overcurrent Release Delay Time	$tV_{REL}3$	V_{DD}=3.0V V-=3V→0V	T_{OPR}= 25℃	3.2	4.0	4.8	ms	F
			T_{OPR}= -30~70℃	2.4	4.0	6.0		
Charge Overcurrent Protection								
Charging Overcurrent Detection Voltage	$V_{DET}4$	V_{DD}=3.5V R2=2.2kΩ	T_{OPR}= 25℃	-0.135	-0.125	-0.115	V	G
			T_{OPR}= -30~70℃	-0.145	-0.125	-0.105		
Charging Overcurrent Detection Current	$I_{DET}4$	# Reference : 1) Discharge / Charge Overcurrent Characteristics						
Charging Overcurrent Detection Delay Time	$tV_{DET}4$	V_{DD}=3.5V V-=0V→-1V	T_{OPR}= 25℃	12.8	16.6	20.4	ms	G
			T_{OPR}= -30~70℃	9.6	16.6	25.0		
Charging Overcurrent Release Delay Time	$tV_{REL}4$	V_{DD}=3.5V V-=-1V→0V	T_{OPR}= 25℃	3.2	4.0	4.8	ms	G
			T_{OPR}= -30~70℃	2.4	4.0	6.0		
Short Protection								
Short Detection Voltage	V_{SHORT}	V_{DD}=3.0V	T_{OPR}= 25℃	0.55	0.80	1.00	V	F
			T_{OPR}= -30~70℃	0.40	0.80	1.10		
Short Detection Delay Time	t_{SHORT}	V_{DD}=3.0V V-=0V→3.0V	T_{OPR}= 25℃	230	400	560	μs	F
			T_{OPR}= -30~70℃	180	400	800		

Note : *1 The test circuit symbols.

*2 The parameter is guaranteed by design.

Item	Symbol	Measure Condition	Min.	Typ.	Max.	Unit	*1
Integrated MOSFET							
Drain-Source Breakdown Voltage	BV_{DSS}	I_D=250㎂, V_{GS}=0V	24	-	-	V	
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=20V, V_{GS}=0V	-	-	1	㎂	
		T_J=55℃	-	-	5		
Gate-Body Leakage Current	I_{GSS}	V_{DS}=0V, V_{GS}=±10V	-	-	10	㎂	
Gate-Source Breakdown Voltage	BV_{GSO}	V_{DS}=0V, I_G=±250㎂	±12	-	-	V	
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250㎂	0.6	1.0	1.5	V	
Static Source-Source ON-Resistance	$R_{SS(ON)}$	V_{GS}=4.4V, I_D=1A	10.0	14.0	18.0	mΩ	
		V_{GS}=4.2V, I_D=1A	10.0	14.0	18.0	mΩ	
		V_{GS}=3.9V, I_D=1A	11.0	15.0	19.0	mΩ	
		V_{GS}=3.7V, I_D=1A	12.0	16.0	20.0	mΩ	
		V_{GS}=3.5V, I_D=1A	13.0	17.0	21.0	mΩ	
		V_{GS}=3.3V, I_D=1A	14.0	18.0	22.0	mΩ	
		V_{GS}=3.0V, I_D=1A	14.0	18.0	22.0	mΩ	
Diode Forward Voltage	V_{SD}	I_S=1A, V_{GS}=0V	0.50	0.69	0.90	V	
Maximum Body-Diode Continuous Current	I_S		-	-	4.5	A	

Note : *1 The test circuit symbols.

*2 The parameter is guaranteed by design.

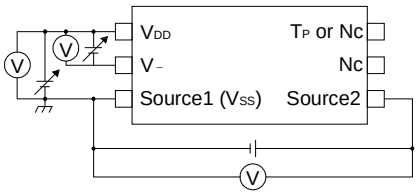
1) Discharge / Charge Overcurrent Characteristics

Item	Symbol	Measure Condition	Min.	Typ.	Max.	Unit	*1
Discharging overcurrent detection Current	I_{DET}3(1)	V_{DD}=4.4V	5.7	8.2	13.5	A	
	I_{DET}3(2)	V_{DD}=4.2V	5.7	8.2	13.5	A	
	I_{DET}3(3)	V_{DD}=3.9V	5.4	7.6	12.3	A	
	I_{DET}3(4)	V_{DD}=3.7V	5.1	7.1	11.3	A	
	I_{DET}3(5)	V_{DD}=3.5V	4.8	6.7	10.4	A	
	I_{DET}3(6)	V_{DD}=3.3V	4.5	6.2	9.6	A	
	I_{DET}3(7)	V_{DD}=3.0V	4.5	6.2	9.6	A	
Charging Overcurrent Detection Current	I_{DET}4(1)	V_{DD}=4.4V	5.7	8.2	13.5	A	
	I_{DET}4(2)	V_{DD}=4.2V	5.7	8.2	13.5	A	
	I_{DET}4(3)	V_{DD}=3.9V	5.4	7.6	12.3	A	
	I_{DET}4(4)	V_{DD}=3.7V	5.1	7.1	11.3	A	
	I_{DET}4(5)	V_{DD}=3.5V	4.8	6.7	10.4	A	
	I_{DET}4(6)	V_{DD}=3.3V	4.5	6.2	9.6	A	
	I_{DET}4(7)	V_{DD}=3.0V	4.5	6.2	9.6	A	

Note : The parameter is guaranteed by design, not tested in production.

Measuring Circuit

A.



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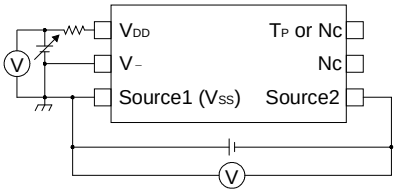

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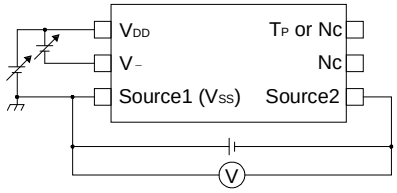

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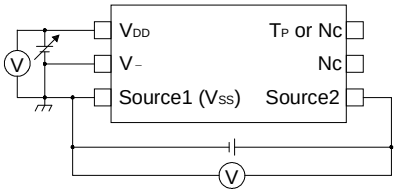

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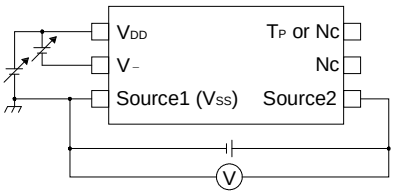

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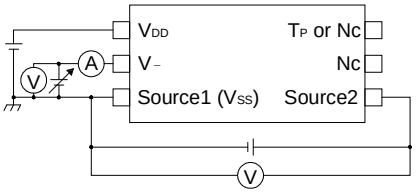

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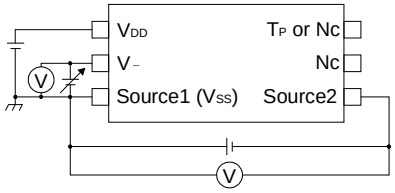

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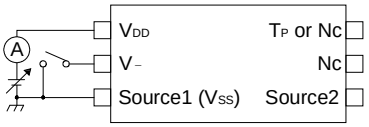


Operation

1. Overcharge detector (VD1)

The VD1 monitors V_{DD} pin voltage during charge. In the state of charging the battery, it will detect the overcharge state of the battery if the V_{DD} terminal voltage becomes higher than the overcharge detection voltage(Typ. 4.425V). And then the C_{OUT} terminal turns to low level, so the internal charging control Nch MOSFET turns OFF and it forbids to charge the battery.

After detecting overcharge, it will release the overcharge state if the V_{DD} terminal voltage becomes lower than the overcharge release voltage(Typ. 4.225V). And then the C_{OUT} terminal turns to high level, so the internal charging control Nch MOSFET turns ON, and it accepts 새 charge the battery.

When the V_{DD} terminal voltage is higher than the overcharge detection voltage, to disconnect the charger and connect the load, leave the C_{OUT} terminal low level, but it accepts to conduct load current via the paracitical body diode of the internal Nch MOSFET. And then if the V_{DD} terminal voltage becomes lower than the overcharge detection voltage, the C_{OUT} terminal turns to high level, so the internal Nch MOSFET turn ON, and it accepts to charge the battery.

The overcharge detection and release have delay time decided internally. When the V_{DD} terminal voltage becomes higher than the overcharge detection voltage, if the V_{DD} terminal voltage becomes lower than the overcharge detection voltage again within the overcharge detection delay time(Typ. 1.00s), it will not detect overcharge. And in the state of overcharge, when the V_{DD} terminal voltage becomes lower than the overcharge release voltage, if the V_{DD} terminal voltage backs higher than the overcharge release voltage again within the overcharge release delay time(Typ. 16ms), it will not release overcharge.

The output driver stage of the C_{OUT} terminal includes a level shifter, so it will output the V_- terminal voltage as low level. The output type of the C_{OUT} terminal is CMOS output between V_{DD} and V_- terminal voltage.

2. Overdischarge detector (VD2)

The VD2 monitors V_{DD} pin voltage during discharge. In the state of discharging the battery, it will detect the overdischarge state of the battery if the V_{DD} terminal becomes lower than the overdischarge detection voltage (Typ. 2.500V). And then the D_{OUT} terminal turns to low level, so the internal discharging control Nch MOSFET turn OFF and it forbids to discharge the battery.

Once overdischarge has been detected, overdischarge is released and the D_{OUT} output becomes high level, if the voltage of the battery rises more than the overdischarge detection voltage with connecting the charger, or more than the overdischarge release voltage without connecting the charger. Charging current is supplied through a parasitic diode of Nch MOS FET when the V_{DD} terminal voltage is below the overdischarge detection voltage to the connection of the charger, and the D_{OUT} terminal enters the state which can be discharged by becoming high level,and turning on Nch MOS FET when the V_{DD} terminal voltage rises more than the overdischarge detection voltage.

When the battery voltage is about 0V, if the charger voltage is higher than the minimum operating voltage for 0V charging (Max. 1.2V), the C_{OUT} terminal outputs high level and it accepts to conduct charging current.

The overdischarge detection have delay time decided internally. When the V_{DD} terminal voltage becomes lower than the overdischarge detection voltage, if the V_{DD} terminal voltage becomes higher than the overdischarge detection voltage again within the overdischarge detection delay time (Typ. 20ms), it will not detect overdischarge. Moreover, the overdischarge release delay time (Typ. 2.8ms) exists, too.

All the circuits are stopped, and after the overdischarge is detected, it is assumed the state of the standby, and decreases the current (standby current) which IC consumes as much as possible. (When V_{DD}=2V, Max. 0.5uA).

The output type of the D_{OUT} terminal is CMOS output between V_{DD} and V_{SS} terminal voltage.

3. Discharge overcurrent detector, Short detector (VD3, Short Detector)

In the state of chargable and dischargabe, VD3 monitors the voltage level of V^- pin. If the V^- terminal voltage becomes higher than the discharging overcurrent detection voltage (Typ. 0.125V) by short of loads, etc., it will detect discharging overcurrent state. If the V^- terminal voltage becomes higher then short detection voltage (Typ. 0.8V), it will detect discharging overcurrent state, too. And then the D_{OUT} terminal outputs low level, so the internal discharging control Nch MOSFET turns OFF, and it protects from large current discharging.

The discharging overcurrent detection has delay time decided internally. When the V^- terminal voltage becomes higher than the discharging overcurrent detection voltage, if the V^- terminal voltage becomes lower than the discharging overcurrent detection voltage within the discharging overcurrent detection delay time (Typ. 12ms), it will not detect discharging overcurrent. Morever, the discharging overcurrent release delay time (Typ. 4ms) exists, too.

The short detection delay time (Typ. 400us) decided internally exists, too.

The discharging overcurrent release resistance is built into between V^- terminal and V_{SS} terminal. In the state of discharging overcurrent or short, if the load is opened, V^- terminal is pulled down to the V_{SS} via the discharging overcurrent release resistance.

And when the V^- terminal voltage becomes lower than the discharging overcurrent detection voltage, it will automatically release discahrging overcurrent or short state. if discharging overcurrent or short is detected, the discharging overcurrent release resistance turns ON. On the normal state (chargable and dischargable state), the discharging overcurrent release resistance is OFF.

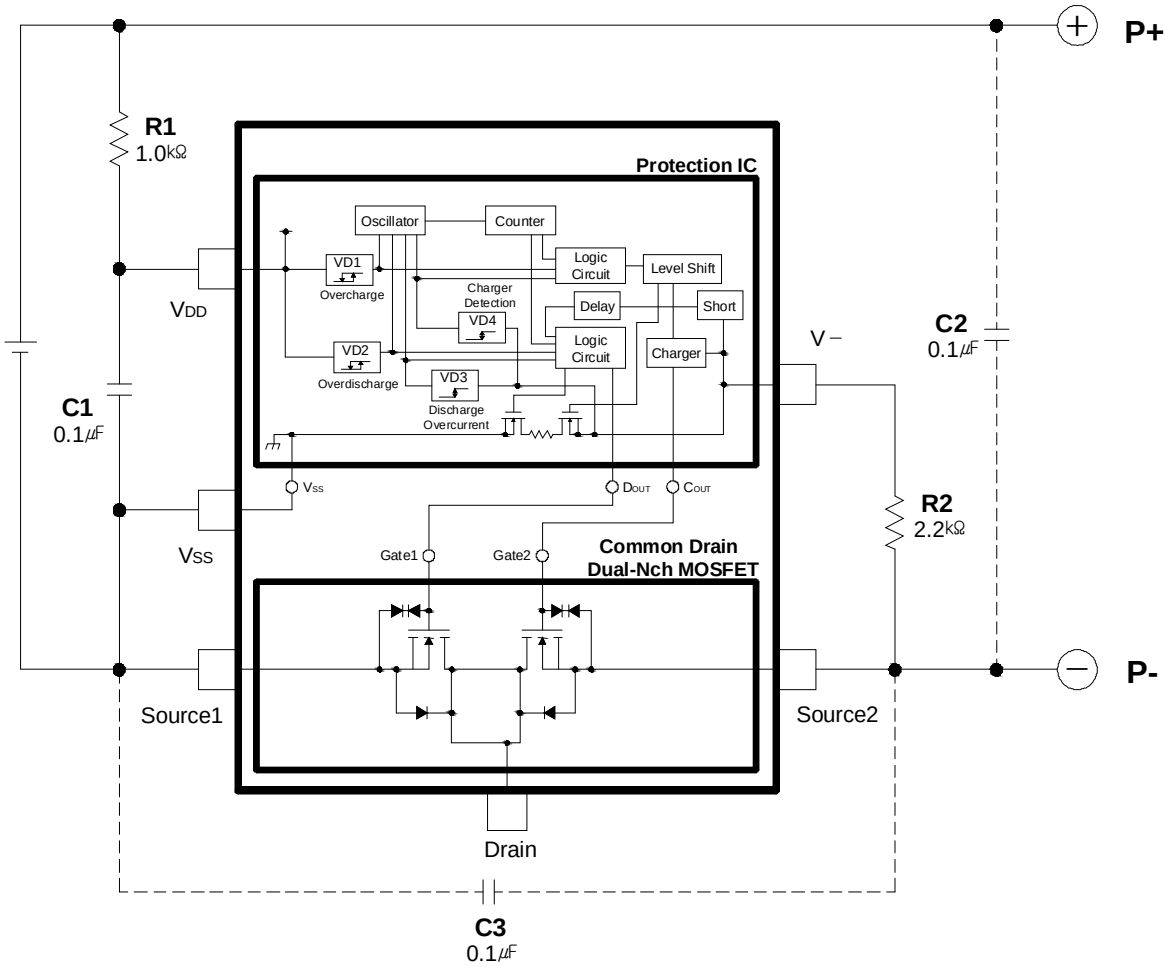
4. Charge overcurrent detector (VD4)

In the state of chargable and dischargable, VD4 monitors the voltage level of V^- pin. If the V^- terminal voltage becomes lower than charging overcurrent detection voltage (Typ. -0.125V) by abnormal voltage or current charger, etc., it will detect charging overcurrent state. And then the C_{OUT} terminal outputs low level, so the internal charging control Nch MOSFET turn OFF, and it protects from large current charging.

It release charging overcurrent state if the abnormal charger is disconnected and the load is connected.

The charging overcurrent detection has delay time decided internally. When the V^- terminal voltage becomes lower than the charging overcurrent detection voltage, if the V^- terminal voltage becomes higher than the charging overcurrent detection voltage within the charging overcurrent detection delay time (Typ. 16.6ms), it will not detect charging overcurrent. Morever, the charging overcurrent release delay time (Typ. 4ms) exists, too.

Application Circuit (Example)



※ Application Hint

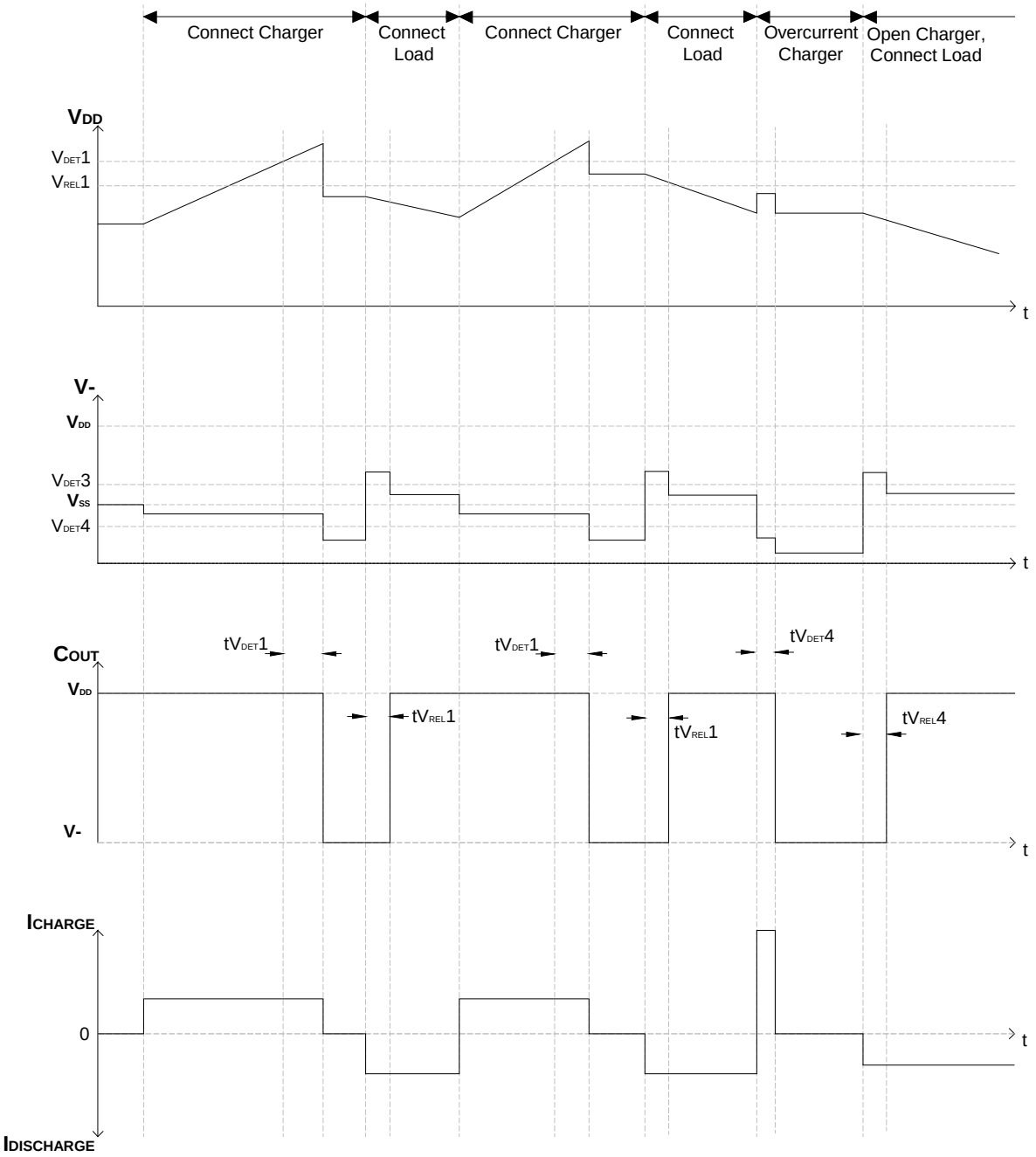
R1 and C1 stabilize a supply voltage ripple. However, the detection voltage rises by the current of penetration in IC of the voltage detection when R1 is enlarged, so the value of R1 is adjusted to 1kohm or less. Moreover, adjust the value of C1 to 0.01uF or more to do the stability operation, please.

R1 and R2 resistors are current limit resistance if a charger is connected reversibly or a highvoltage charger that exceeds the absolute maximum rating is connected. R1 and R2 may cause a power consumption will be over rating of power dissipation, therefore the `R1+R2` should be more than 1kohm. Moreover, if R2 is too enlarged, the charger connection release cannot be occasionally done after the overdischarge is detected, so adjust the value of R2 to 10kohm or less, please.

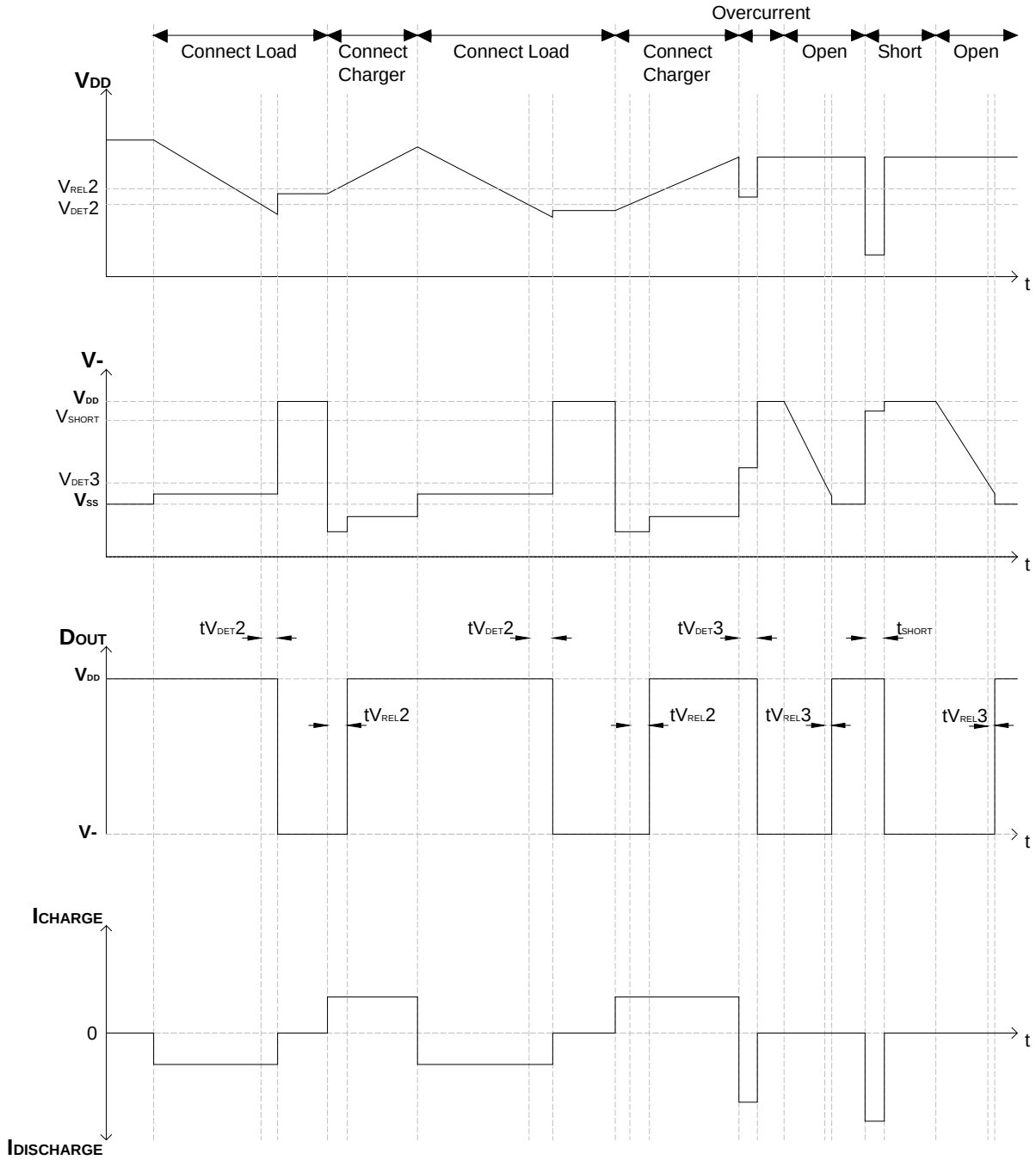
C2 and C3 capacitors have effect that the system stability about voltage ripple or imported noise. After check characteristics, decide that these capacitors should be inserted or not, where should be inserted, and capacitance value, please.

Timing Chart

1. Overcharge, Charging overcurrent operations

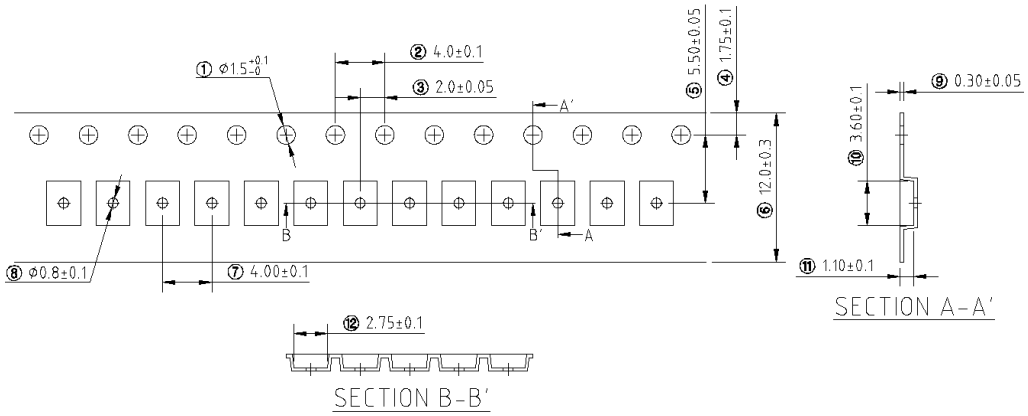


2. Overdischarge, Discharging Overcurrent and Short operations

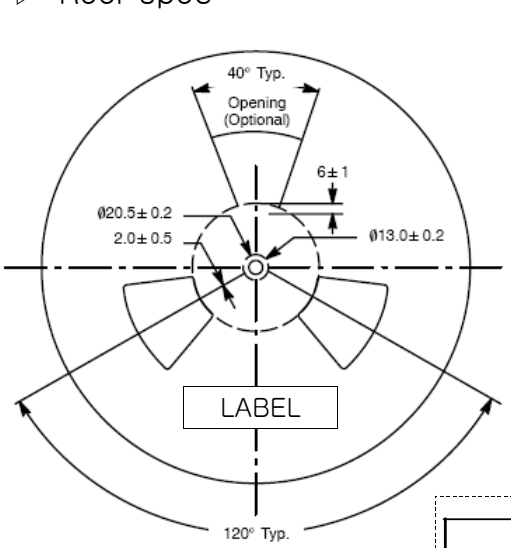


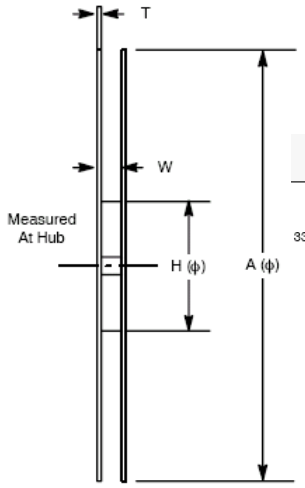
Packing spec

▷ Carrier tape spec



▷ Reel spec



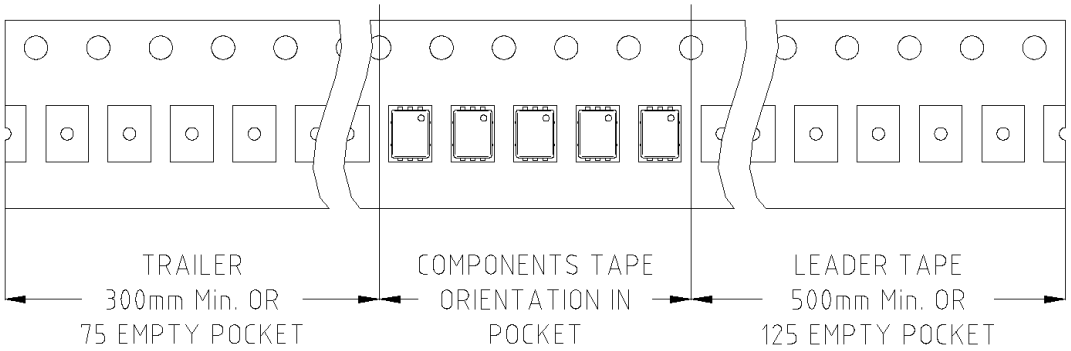


A	W		TAPE WIDTH	H	T
330±2	16.4	+2.0 −0	16	100±1	2.5±0.5

REEL LABEL

Model Name : *"Barcode"*	Q'ty : *"Barcode"*	ITM RoHS HF
Made Date : *"Barcode"*	Lot No : *"Barcode"*	

▷ Taping spec



▷ OUTER BOX PACKING SPECIFICATION

OUT BOX LABEL

ITM ITM Semiconductor Co., Ltd

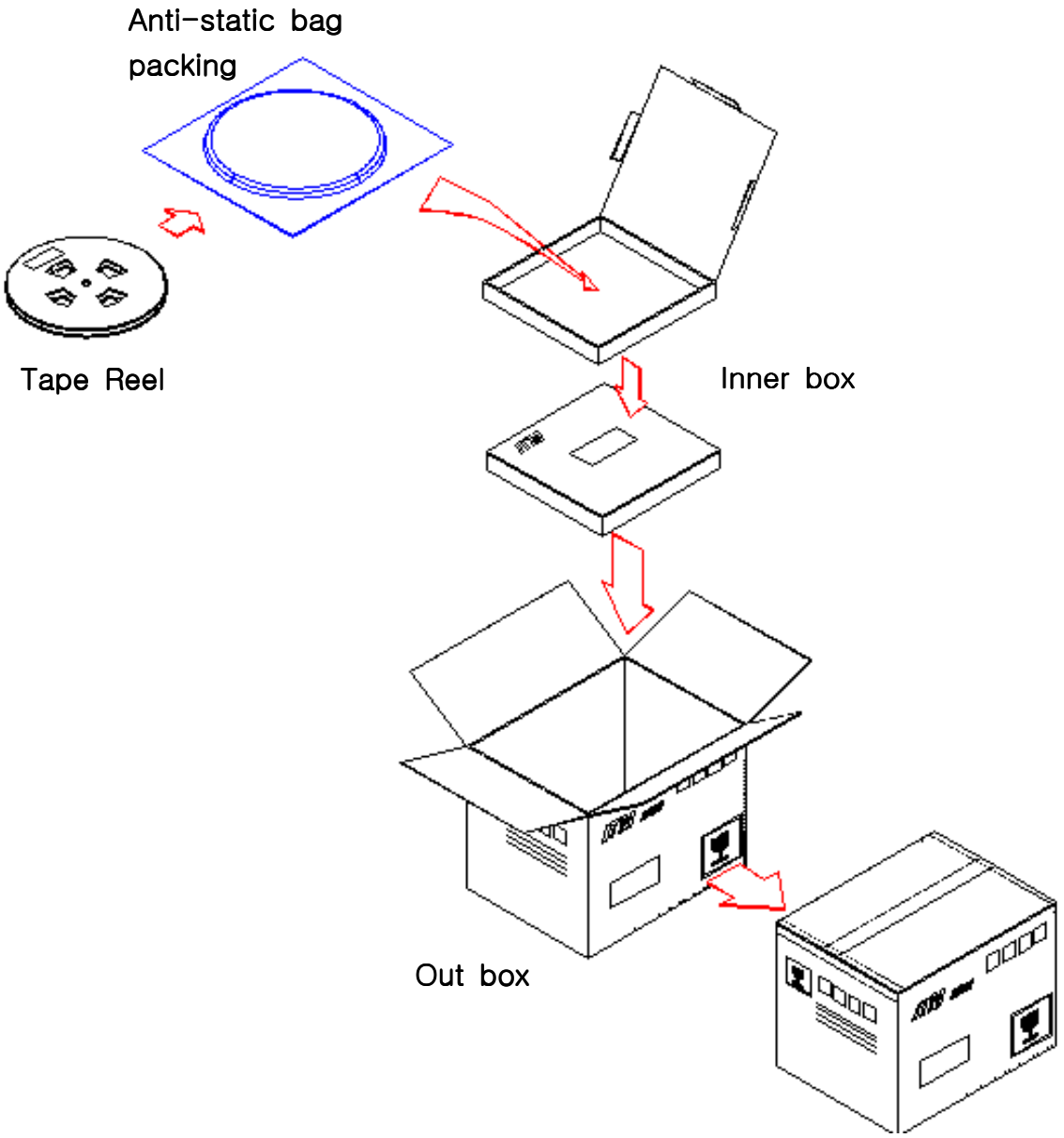
Model Name : *"Barcode"*

Q'ty : *"Barcode"*

RoHS HF

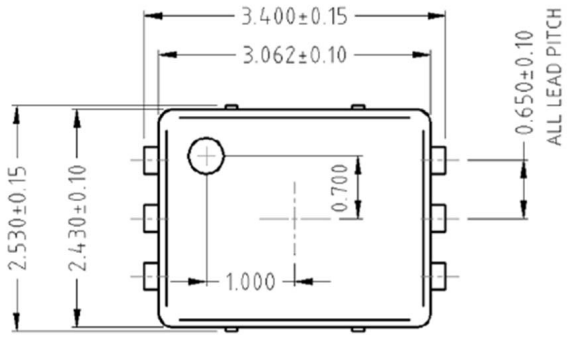
Ship Date : *"Barcode"*

Lot No : *"Barcode"*

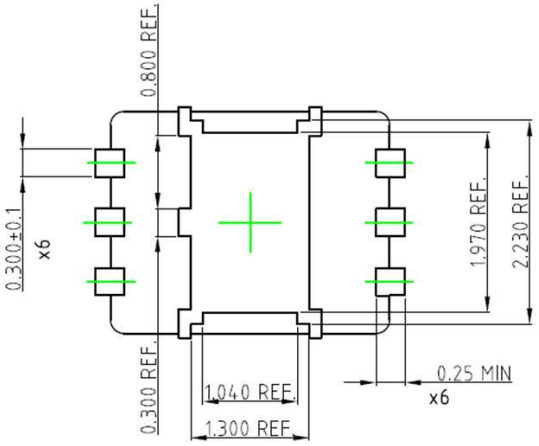


Package Description

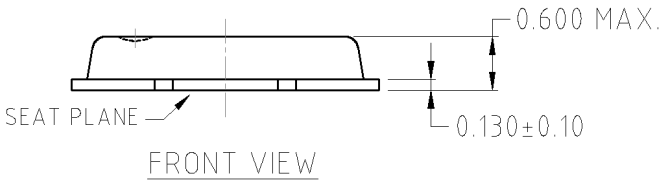
■ TOP VIEW



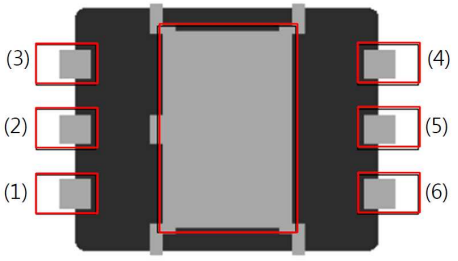
■ BOTTOM VIEW

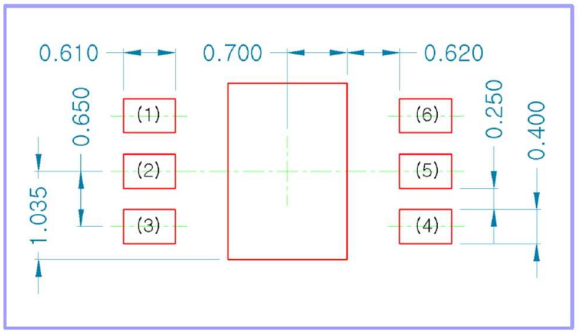


■ FRONT VIEW



Recommend Land Pattern





[mm]

Marking Contents